

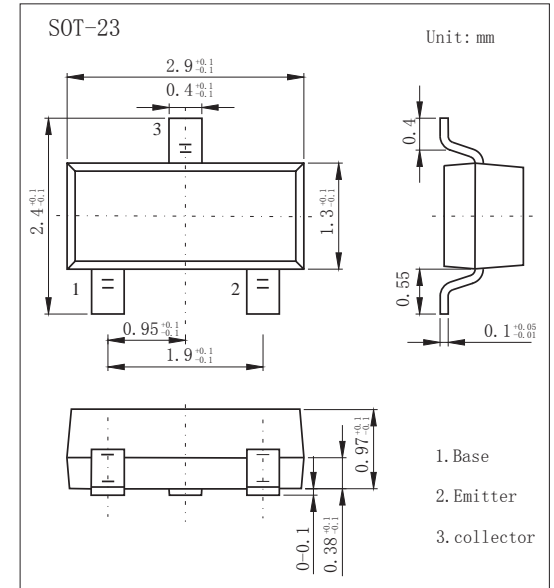
SOT-23 Plastic-Encapsulate Transistors

Features

- Complementary to S9014
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _c	-0.1	A
Collector Power Dissipation	P _c	0.2	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

PACKAGE INFORMATION

Device	Package	Shipping
S9015	SOT-23	3000/Tape&

Electrical Specification (T_A=25@25°C unless otherwise specified)

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =-100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{CEO}	I _c =-1mA, I _B =0	-45			V
Emitter-base Breakdown voltage	V _{EB0}	I _E =-100 μA, I _C =0	-5			V
Collector cutoff current	I _{CB0}	V _{CB} =-50V, I _E =0			-0.1	μ A
Emitter cutoff current	I _{EB0}	V _{EB} =-5V, I _C =0			-0.1	μ A
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=30MHZ	150			MHz

■ hFE Classification

Type	S9015-L	S9015-H
Range	200-450	450-1000
Marking	M6	